2:8 7000	Application No.	Applicant(s)	
	09/920,222	DAVIES, ROBERT B.	
Notice of Allowability	Examiner	Art Unit	
	Eugene Lee	2815	
The MAILING DATE of this communication appeal claims being allowable, PROSECUTION ON THE MERITS IS (Gerewith (or previously mailed), a Notice of Allowance (PTOL-85) of IOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHT of the Office or upon petition by the applicant. See 37 CFR 1.313	OR REMAINS) CLOSED in this apport of the communication The communication is subject to the co	will be mailed in due course. THIS	ive
. This communication is responsive to <u>12/27/05</u> .			
 ∴ The allowed claim(s) is/are <u>1,2,4-7,37 and 39-48</u>. 			
Acknowledgment is made of a claim for foreign priority und a) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have 3. Copies of the priority documents have 4. Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE" of noted below. Failure to timely comply will result in ABANDONMITHIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 4. A SUBSTITUTE OATH OR DECLARATION must be submited in INFORMAL PATENT APPLICATION (PTO-152) which give in Including changes required by the Notice of Draftsperson of the including changes required by the Notice of Draftsperson of the including changes required by the attached Examiner's Paper No./Mail Date (b) including changes required by the attached Examiner's Paper No./Mail Date tentifying indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in the deposit of the priority documents and the deposit of the deposit of the priority documents and the deposit of the priority documents and the priority documents and the deposit of the priority documents and	been received. been received in Application No uments have been received in this of this communication to file a reply ENT of this application. tted. Note the attached EXAMINER is reason(s) why the oath or declar t be submitted. on's Patent Drawing Review (PTO is Amendment / Comment or in the (attached EXAMINER is reason(s) why the oath or declar to be submitted. is Amendment / Comment or in the (attached EXAMINER is to file of BIOLOGICAL MATERIAL	complying with the requirements S AMENDMENT or NOTICE OF ation is deficient. 948) attached Office action of lings in the front (not the back) of (d). must be submitted. Note the	
Attachment(s) 1. Notice of References Cited (PTO-892) 2. Notice of Draftperson's Patent Drawing Review (PTO-948) 3. Information Disclosure Statements (PTO-1449 or PTO/SB/Paper No./Mail Date	6. ☐ Interview Summar Paper No./Mail D 7. ☑ Examiner's Amend	ate Iment/Comment	
Paper No./Mail Date	8. 🛭 Examiner's Staten	nent of Reasons for Allowance	
of Biological Material	9. 🔲 Other		
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DETAILED ACTION

Examiner's Amendment

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows:

Claims 8 thru 27, and 34 thru 36, previously withdrawn from consideration for being drawn towards a non-elected invention, have been cancelled.

Allowable Subject Matter

- 2. Claims 1, 2, 4 thru 7, 37, and 39 thru 48 are allowed.
- 3. The following is an examiner's statement of reasons for allowance: The references of record, either singularly or in combination, do not teach or suggest at least an integrated circuit, comprising: a low resistivity semiconductor substrate having a dielectric region formed therein, a trench; an adjacent cavity; an electroplated conductive material disposed within the trench to produce an inductance; a bottom surface of the semiconductor substrate defining a first recessed region underlying the dielectric region (claims 1, 2, and 4-7).

Regarding claims 37, 41, and 42, the references of record, either singularly or in combination, do not teach or suggest at least an integrated circuit comprising: a low resistivity, semiconductor substrate including a dielectric region; a trench formed in the dielectric region; high conductivity electroplated material in the trench and defining at least a portion of a passive

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electronic component, wherein the low dielectric constant material includes dielectric material defining an array of cavities therein, the dielectric material having a first dielectric constant and the cavities providing a second dielectric constant lower than the first dielectric constant to form an effective dielectric constant lower than the first dielectric constant.

Regarding claims 39, and 40, the references of record, either singularly or in combination, do not teach or suggest at least an integrated circuit comprising: a low resistivity, semiconductor substrate including a dielectric region; a trench formed in the dielectric region and including side-walls defined by low dielectric constant material; high conductivity electroplated material in the trench and defining at least a portion of a passive electronic component; and wherein the low dielectric constant material includes dielectric material defining an array of cavities therein, the dielectric material having a first dielectric constant and the cavities providing a second dielectric constant lower than the first dielectric constant to form an effective dielectric constant lower than the first dielectric constant.

Regarding claims 43, and 44, the references of record, either singularly or in combination, do not teach or suggest at least an integrated circuit comprising: a low resistivity, semiconductor substrate including a dielectric region; a trench formed in the dielectric region; high conductivity electroplated material in the trench and defining at least a portion of a passive electronic component; and further including a cavity at least partially defined by the substrate in the dielectric region and in communication with a lower portion of the high conductivity, electroplated material in the trench.

Regarding claims 45-48, the references of record, either singularly or in combination, do not teach or suggest at least an integrated circuit comprising: a low resistivity, semiconductor

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substrate including a dielectric region; an elongated trench formed in the dielectric region; high conductivity material in the trench and defining at least a portion of an inductive component; and a sealed cavity at least partially defined by the substrate in the dielectric region and in communication with a lower portion of the high conductivity material in the trench.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

INFORMATION ON HOW TO CONTACT THE USPTO

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Eugene Lee whose telephone number is 571-272-1733. The examiner can normally be reached on M-F 8-5.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Kenneth Parker can be reached on 571-272-2298. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

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